

High- h_{FE} High V_{EBO} Transistors

High- h_{FE} , High- V_{EBO} Transistors

Features

- * High h_{FE} (500 to 3200)
- * High $V_{EBO} \geq 15V$
- * Low saturation voltage ($V_{CE(sat)} \leq 0.5V$)
- * Very small package permitting audio/video sets to be made smaller, slimmer

Applications

- * AF amp
- * Driver
- * Muting circuit

1:Base
2:Emitter
3:Collector

Case outlines (unit:mm)

SANYO:MCP
1:B, 2:E, 3:C

SANYO:CP

1:B, 2:E, 3:C

SANYO:PCP

1:B, 2:C, 3:E

SANYO:SPA

1:Emitter, 2:Collector, 3:Base

SANYO:NP

1:E, 2:C, 3:B

SANYO:MP

1:E, 2:C, 3:B

SANYO:TP

1:Base, 2:Collector, 3:Emitter,

4:Collector

SANYO:FLP

1:E, 2:C, 3:B

SANYO:TO-126LP

1:E, 2:C, 3:B

©:Resistance-Contained (2SC4909:R1=47K Ω , R2=47K Ω)

For PNP, (-) sign is omitted. * sign $T_c=25^\circ C$. ☆ sign Mounted on ceramic board (250mm $\times$ 0.8mm).

Type No.	Package	Absolute Maximum Ratings/ $T_a=25^\circ C$						Electrical Characteristics/ $T_a=25^\circ C$						
		V_{CBO} (V)	V_{CEO} (V)	V_{EBO} (V)	I_C (A)	P_C (W)		V_{CE} (V)	I_C (mA)	h_{FE}	I_C (mA)	I_B (mA)	$V_{CE(sat)}$ V_{typ} (V)	$V_{CE(sat)}$ V_{max} (V)
2SC4919(DA)	SMCP	25	15	5	0.1	0.15		2	5	800 ~ 3200	10	1	14m	30m
2SA1813(KS)	MCP	30	25	15	0.15	0.15		5	1	500 ~ 1200	50	1	0.15	0.3
2SC4413(GY)		60	50	15	0.1	0.15		5	10	800 ~ 3200	50	1	0.1	0.5
2SC4851(YT)		25	15	5	0.1	0.2		2	5	800 ~ 3200	10	1	14m	30m
2SC4909(JN)©		25	20	10	0.1	0.2		2	5	200	2	0.2	10m	30m
2SA1434(FL)	CP	60	50	15	0.1	0.2		5	10	500 ~ 1200	50	1	0.2	0.5
2SC3689(GY)										800 ~ 3200			0.1	
2SA1814(KS)		30	25	15	0.15	0.2		5	1	500 ~ 1200	50	1	0.15	0.3
2SC3661(FY)		30	25	15	0.3	0.2		5	10	800 ~ 3200	200	4	0.12	0.5
2SC4852(YT)	PCP	25	15	5	0.1	0.25		2	5	800 ~ 3200	10	1	14m	30m
2SA1766(AL)		30	25		0.3	☆1.3		5	10	500 ~ 1200	200	4	0.12	0.5
2SC3650(CF)		30	25		1.2	☆1.5		5	500	800 ~ 3200	500	10	0.12	0.5
2SC3651(CG)		120	100		0.2	☆1.3		5	10	500 ~ 2000	100	2	0.15	0.5
2SC4390(CJ)	SPA	20	10		2	☆1.3		2	500	800 ~ 3200	1000	20	0.11	0.3
2SC4705(CP)		60	50		0.2	☆1.3		5	100	800 ~ 3200	100	2	0.12	
2SC5069(CU)		30	25		2	☆1.5		5	500	800 ~ 3200	1000	20	0.15	
2SC3576		30	25		0.3	0.3		5	10	800 ~ 3200	200	4	0.12	
2SC3820	NP	60	50		0.1	0.3		5	10	800 ~ 3200	50	1	0.1	
2SA1435		30	25		0.3	0.6		5	10	500 ~ 1200	200	4	0.18	
2SC3068				15						800 ~ 3200			0.12	
2SA1436		60	50		0.2	0.6		5		500 ~ 1200			0.2	
2SC3069	TP	120	100		50m	0.5		5	10	400 ~ 1000	10	0.2	0.18	
2SA1437										500 ~ 2000			0.1	
2SC3495														
2SC4204		30	25		0.7	0.6		5	50	800 ~ 3200	500	10	0.15	
2SA1562	MP	30	25		1.2	*15		5	100	500 ~ 1200	500	10	0.1	
2SC5155		50	20		3	*20		2	500	800 ~ 3200	2000	20	0.15	
2SC3070		30	25		1.2	1		5	500	800 ~ 3200	500	10	0.12	
2SC3071		120	100		0.2	1		5	10	500 ~ 2000	100	2	0.15	
2SC4736	FLP	80	60		2	1.5		5	500	800 ~ 3200	1000	20	0.2	
2SC5070		30	25		2	1.5		5	500	800 ~ 3200	1000	20	0.15	
2SA1692		30	25		2	*15		5	100	500 ~ 1200	1000	20	0.15	
2SC3807										500 ~ 3200				
2SC3808	TO-126LP	80	60		2	*15		5	500	800 ~ 3200	1000	20	0.2	

High- V_{EBO} Transistors

Features

- * Highly resistant to surge voltage because of high V_{EBO} .
- * Highly resistant to breakdown because of wide ASO.

For PNP, (-) sign is omitted.

2SA1687(D)	MCP	60	50	15	0.15	0.15	6	1	135 ~ 600	50	5	0.25	
2SC4446(H)												0.15	
2SC4694(WT)	CP	50	20	25	0.5	0.15	5	10	300 ~ 1200	100	2	0.12	
2SA1252(D-)		60	50	15	0.15	0.2	6	1	100 ~ 560	50	5	0.2	
2SC3134(H-)												0.15	
2SC4695(WT)		50	20	25	0.5	0.25	5	10	300 ~ 1200	100	2	0.12	
2SA1253	SPA	60	50	15	0.2	0.25	6	1	100 ~ 560	50	5	0.2	
2SC3135												0.15	
2SA1246		60	50	15	0.15	0.4	6	1	100 ~ 560	50	5	-	
2SC3114												-	
2SC3792	NP	50	20	25	0.5	0.5	5	10	300 ~ 1200	100	2	0.12	

These specifications are subject to change without notice.